

Title (en)

METHOD FOR FORMING, ON A SINGLE SUBSTRATE, TRANSISTORS HAVING DIFFERENT CHARACTERISTICS

Title (de)

VERFAHREN ZUR HERSTELLUNG VON TRANSISTOREN, DIE UNTERSCHIEDLICHE EIGENSCHAFTEN AUFWEISEN, AUF DEMSELBEN SUBSTRAT

Title (fr)

PROCÉDÉ DE RÉALISATION SUR UN MÊME SUBSTRAT DE TRANSISTORS PRÉSENTANT DES CARACTÉRISTIQUES DIFFÉRENTES

Publication

EP 3246953 B1 20190320 (FR)

Application

EP 17171987 A 20170519

Priority

FR 1654556 A 20160520

Abstract (en)

[origin: US2017338157A1] A method is provided for producing at least one first transistor and at least one second transistor on the same substrate, including producing at least one first gate pattern and at least one second gate pattern on the substrate; depositing at least one first protective layer on the first and the second gate patterns; depositing, on the first and the second gate patterns, at least a first protective layer and a second protective layer overlying, the first protective layer, the second protective layer being made from a different material than that of the first protective layer; masking the second gate pattern by a masking layer; isotropic etching of the second protective layer; removing the masking layer; and anisotropic etching of the second protective layer selectively relative to the first protective layer.

IPC 8 full level

H01L 29/66 (2006.01); **H01L 21/311** (2006.01); **H01L 21/3115** (2006.01); **H01L 21/32** (2006.01); **H01L 21/8234** (2006.01); **H01L 21/8238** (2006.01); **H01L 21/84** (2006.01); **H01L 27/12** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP US)

H01L 21/31111 (2013.01 - EP US); **H01L 21/31116** (2013.01 - EP US); **H01L 21/32** (2013.01 - US); **H01L 21/823468** (2013.01 - EP US); **H01L 21/823864** (2013.01 - EP US); **H01L 21/84** (2013.01 - EP US); **H01L 27/1203** (2013.01 - EP US); **H01L 29/6656** (2013.01 - EP US); **H01L 29/66628** (2013.01 - EP US); **H01L 21/31155** (2013.01 - EP US); **H01L 27/092** (2013.01 - EP US)

Cited by

EP3783643A1; FR3100085A1; US11244868B2

Designated contracting state (EPC)

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DOCDB simple family (publication)

EP 3246953 A1 20171122; **EP 3246953 B1 20190320**; FR 3051598 A1 20171124; FR 3051598 B1 20181005; US 10026657 B2 20180717; US 2017338157 A1 20171123

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